

**The XII Front-End Electronics Workshop,
Torino 12-16 June 2023**

The TimeSPOT pixel front-end IC in 28-nm CMOS

Adriano Lai
INFN Cagliari



Requirements (and challenges) for 4D-Tracking

1. Space Resolution $\sigma_s \approx 10 \mu\text{m}$ (\rightarrow pixel pitch $\approx 40\text{--}60 \mu\text{m}$)
2. Time Resolution $\sigma_t \leq 50 \text{ ps}$ on the full chain ($\sigma_t = \sigma_{\text{sensor}} \oplus \sigma_{\text{FE}} \oplus \sigma_{\text{TDC}}$). Safety margin: $\approx 30\text{--}40 \text{ ps}$ before irradiation (?)
3. Radiation hardness to high fluences (for sensors) and high doses (for electronics). Fluences $\Phi = 10^{16} \div 10^{17} \text{ 1 MeV } n_{\text{eq}}/\text{cm}^2$ and Doses $> 1 \div 2 \text{ Grad}$
4. The material budget per layer must be kept below $1 \div 0.5 \%$ radiation length
5. A detection efficiency of $\varepsilon > 99\%$ per layer is typically required (high fill factor)
6. Huge data bandwidth $> 100 \text{ Gbps}$ per ASIC

Design in CMOS 28nm appears as a mandatory path, due to its superior integration capabilities and radiation resistance ($\geq 1 \text{ Grad}$). **BUT we have serious technology/operational limitations, especially against timing performance:**

- a. High time resolution @ limited power budget $\approx 10 \mu\text{W}/\text{pixel}$
- b. Limited headroom for supply (0.9 V)
- c. Limited intrinsic MOST g_m (with respect to SiGe Bipolar, for example)
- d. Significant IR drop (issues in global design aspects)



source:
 Considerations for the VELO detector at the LHCb upgrade II – CERN-LHCb-2022-001

Requirement	scenario S_A	scenario S_B
Pixel pitch [μm]	≤ 55	≤ 42
Lifetime fluence [$1 \times 10^{16} \text{ 1 MeV } n_{\text{eq}}/\text{cm}^2$]	> 6	> 1
TID lifetime [MGy]	> 28	> 5
Sensor Timestamp per hit [ps]	≤ 35 *	≤ 35
ASIC Timestamp per hit [ps]	≤ 35 *	≤ 35
Hit Efficiency [%]	≥ 99	≥ 99
Power per pixel [μW]	≤ 23	≤ 14
Pixel rate hottest pixel [kHz]	> 350	> 40
Max discharge time [ns]	< 29	< 250
Bandwidth per ASIC of 2 cm^2 [Gb/s]	> 250	> 94

Material budget $\leq 0.8\% X_0$ per station (all included)

*Corresponds to $< 50 \text{ ps}$ on sensor+electronics



TimeSPOT ASIC developments

Purpose and scope: the high-intensity-4D challenge

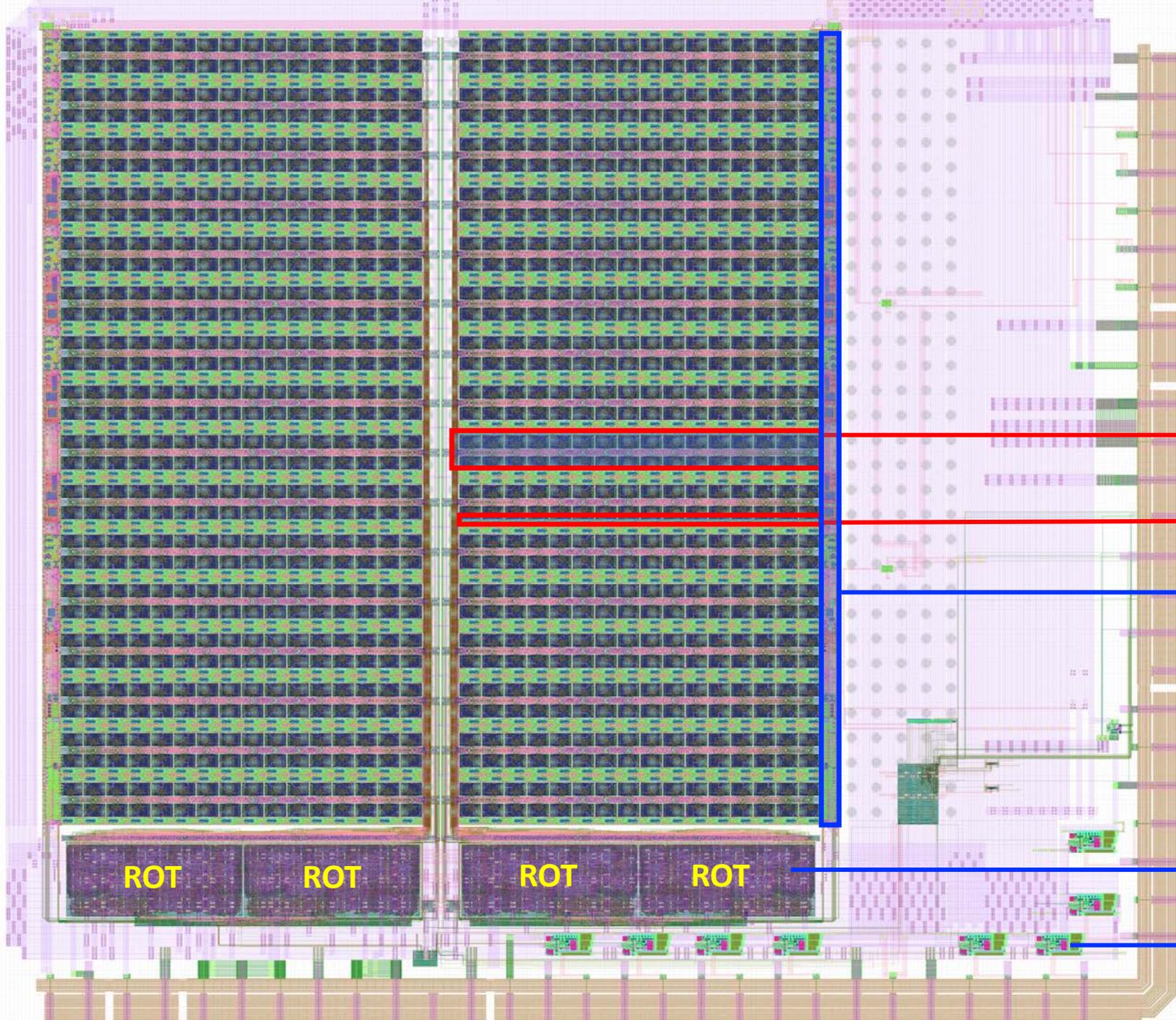


1. Explore the capabilities and technical pitfalls of CMOS 28-nm, which has been chosen as the successor of 65 nm for future HEP developments
2. **Concentrate first on pixel performance** by addressing the questions:
 - What can be integrated in a pixel $\approx 50 \times 50 \mu\text{m}^2$?
 - Referred to a target $\sigma_t \approx 30 \text{ ps}$ ($\sigma_{FE} \oplus \sigma_{TDC}$), what is the minimum power required?
 - What is the maximum sustainable rate/pixel – or – is it possible to integrate 1 TDC per pixel?
 - What would be the best TDC resolution and its power consumption?
3. **Design and produce the largest possible chip, compatibly with time and money budget (32x32 pixels was the choice)**
4. Drop for now the requirement about high data bandwidth, which will surely need specific additional developments (as Silicon Photonics)

2 submissions made:

Timespot0 (single test-cells)

Timespot1 (complete matrix)



Timespot1 ASIC

28-nm CMOS

- Reduced size (1024 pixels, 6 mm²)
- HPC flavour
- Complete set of functionalities for pixel readout
- Slow read-out (demo-test purpose)
- No SEE protection

640 MHz master clock

→ Digital row: 16x2 TDC
+ Controls, Conf. registers, I²C I/F

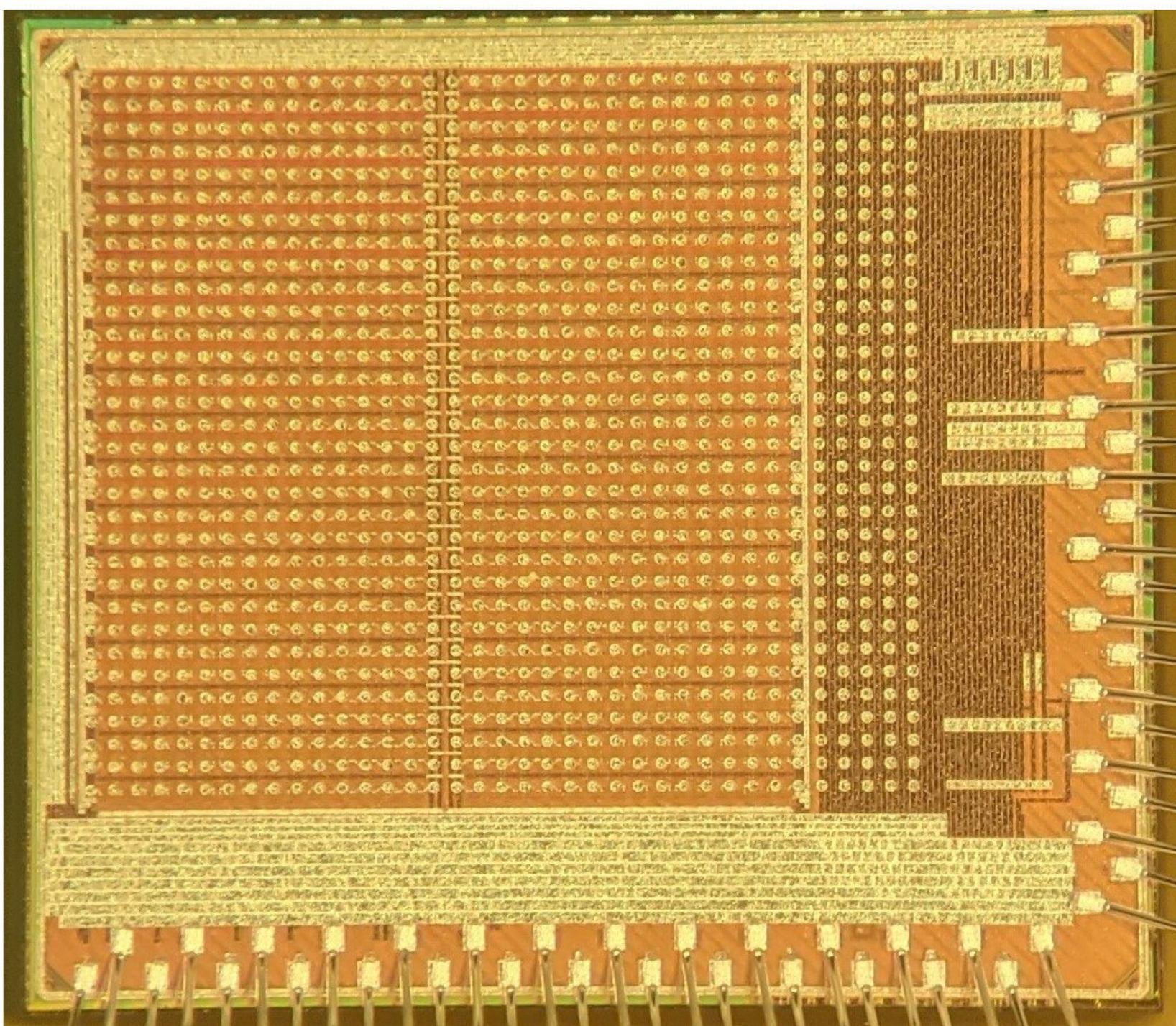
→ Analog row (16x2 AFE)

→ Analog (service) column.
Each contains:

- 1 Band-Gap circuit
- 5x Σ - Δ DACs (producing analog levels used by pixels)
- Programmable bias cell (for power consumption)
- bias replicas with source followers.

→ 4x Read Out Trees

→ 8x LVDS driver
(each @1.28 Gbps)



Timespot1 ASIC

28-nm CMOS

- Reduced size (1024 pixels, 6 mm²)
- HPC flavour
- Complete set of functionalities for pixel readout
- Slow read-out (demo-test purpose)
- No SEE protection

640 MHz master clock

→ Digital row: 16x2 TDC
+ Controls, Conf. registers, I²C I/F

→ Analog row (16x2 AFE)

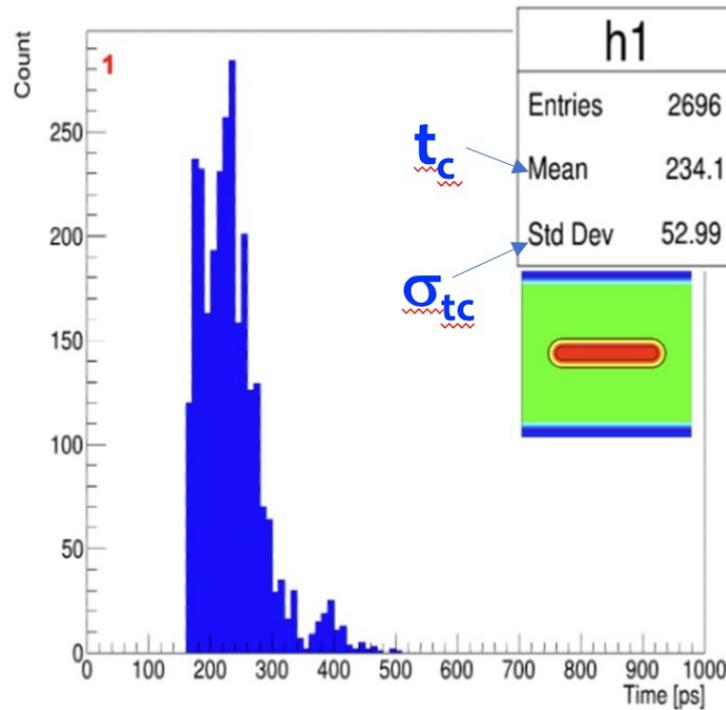
→ Analog (service) column.
Each contains:

- 1 Band-Gap circuit
- 5x Σ - Δ DACs (producing analog levels used by pixels)
- Programmable bias cell (for power consumption)
- bias replicas with source followers.

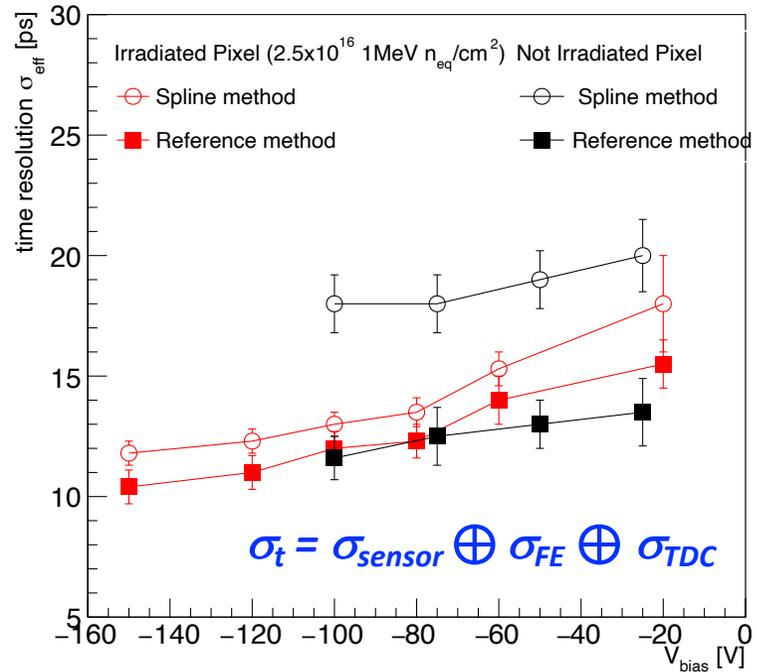
→ 4x Read Out Trees

→ 8x LVDS driver
(each @1.28 Gbps)

4D-pixel performance and related electronics

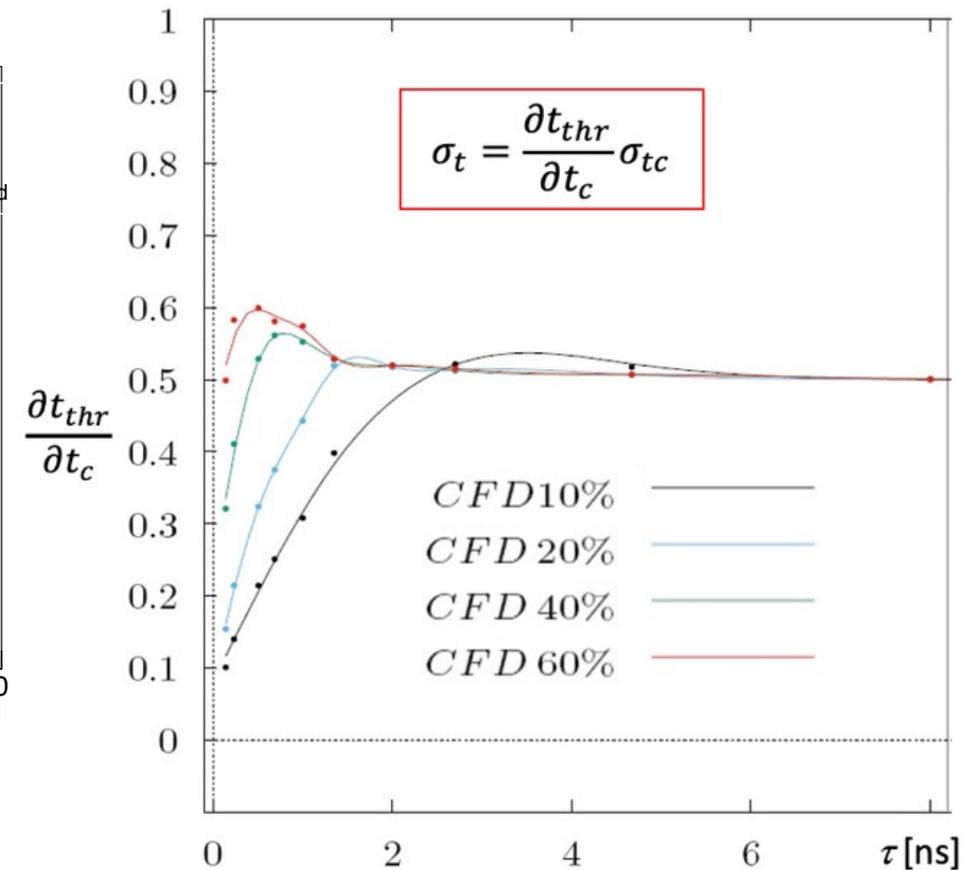


Charge Collection Time of
3D-trench pixel



Timing performance with HBT (Si-Ge) and trans-impedance amplifier stages (high BW, high power)

G. M. Cossu and A. Lai, “Front-end Electronics for Timing with pico-seconds precision using Solid State Sensors”, JINST, vol. 18, 2023
 A. Lai and G. M. Cossu, “High-resolution timing electronics for fast pixel sensors”, arXiv2008.09867, 2020
 W. Riegler and G. A. Rinella, “Time resolution of silicon pixel sensors,” JINST, vol. 12, 2017



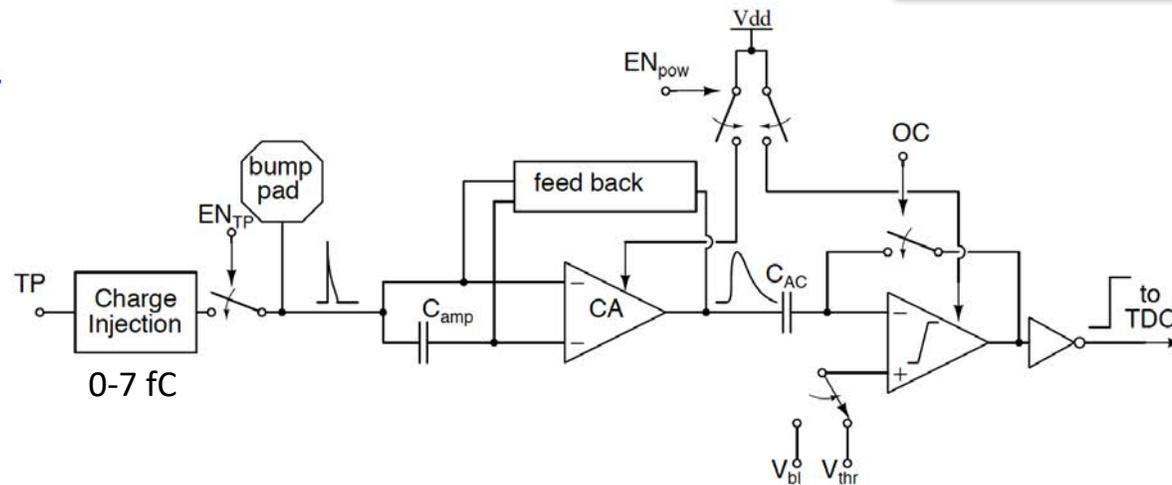
Time resolution vs std. dev. of CCT distribution
Fraction of rms is 1/2 for “slow” electronics (CSA)

With TimeSPOT sensors, 20-25 ps of resolution are theoretically feasible also with the CSA approach

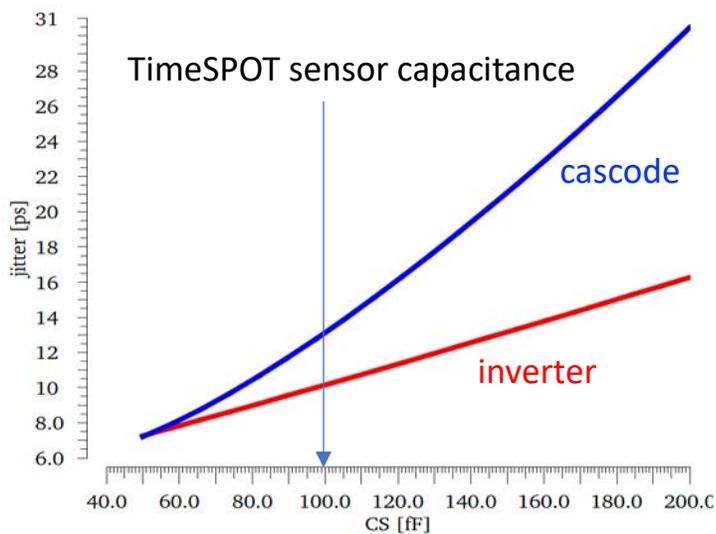
Timespot1: Analog Front End

Inverter core amplifier with double Krummenacher FB

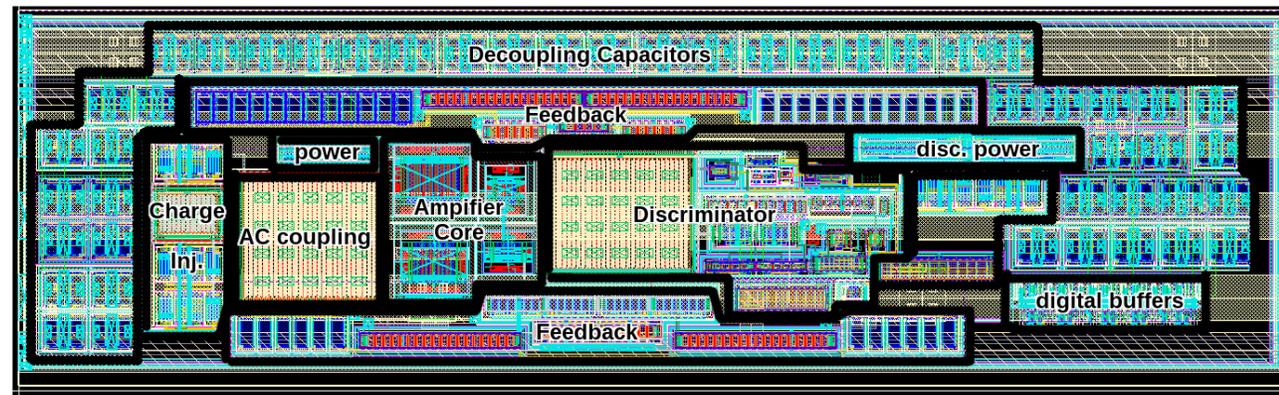
- Charge Sensitive Amplifier (CSA) with DC current compensation (2 Krummenacher filter paths N,P) and constant current discharge
- Leading Edge Discriminator (LED) with Discrete-time Offset-Compensation (OC) for threshold uniformity. OC procedure: 250 ns every $\leq 800 \mu s$
- Cascoded inverter used as core amplifier instead of classical telescopic cascode: almost doubles g_m and OLG
- Higher g_m : higher slew rate, less capacitance sensitivity of time jitter



L. Piccolo – INFN Torino



Post-layout simulations



50x15 μm^2

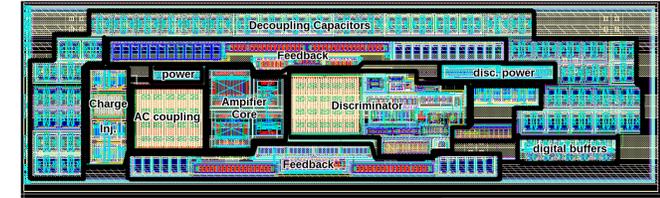
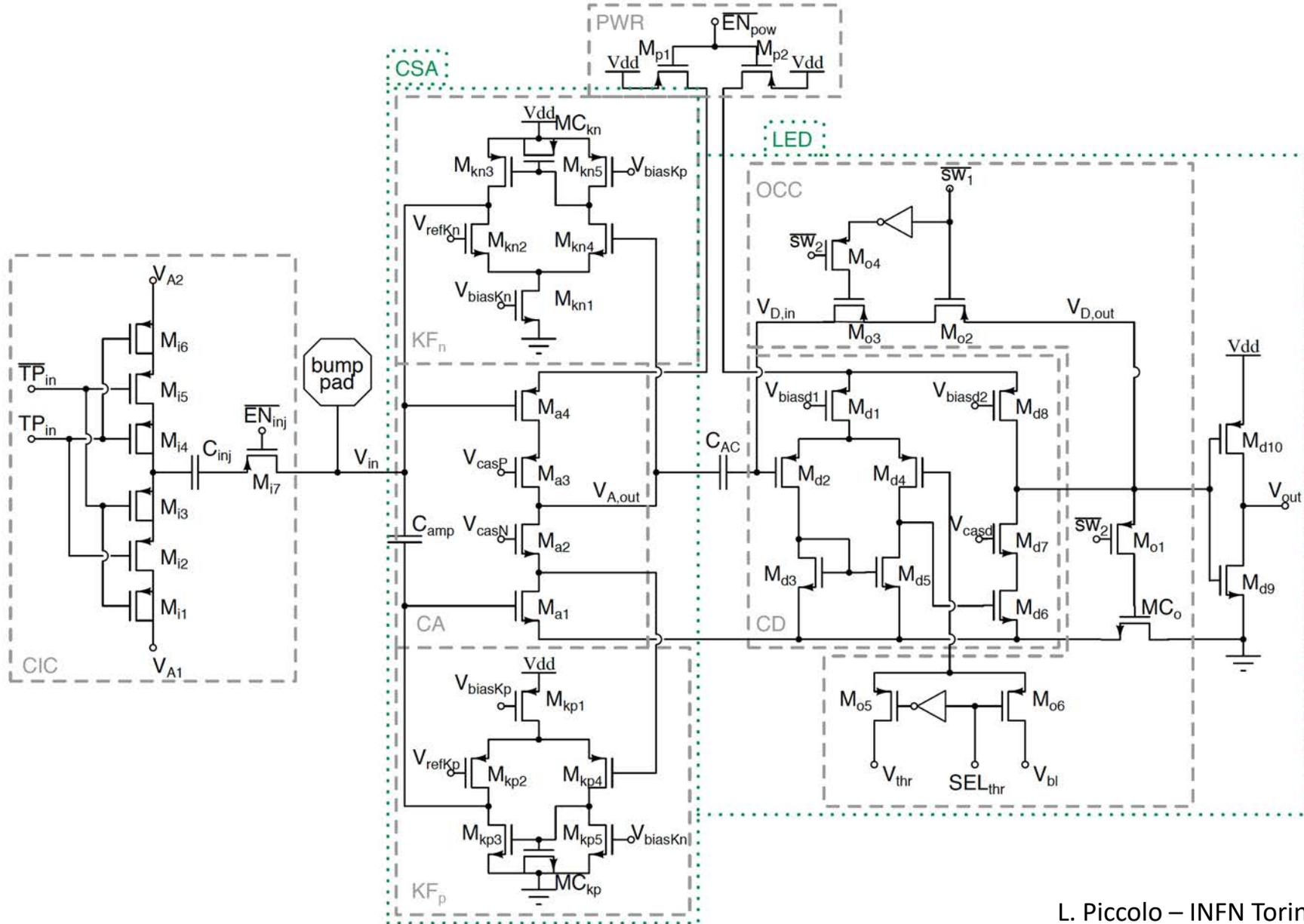
Expected from post-layout simulations:

- 15-20 ps jitter (CSA + LED)
- 12 μW – programmable from 2.3 μW to 32 μW
- (Individual channels can be powered off)

Timespot1 ASIC: transistor level Analog Front End



28nm Timespot ASIC – A. Lai – XII FEE Workshop – Torino, 12/16 June 2023



50x15 μm^2



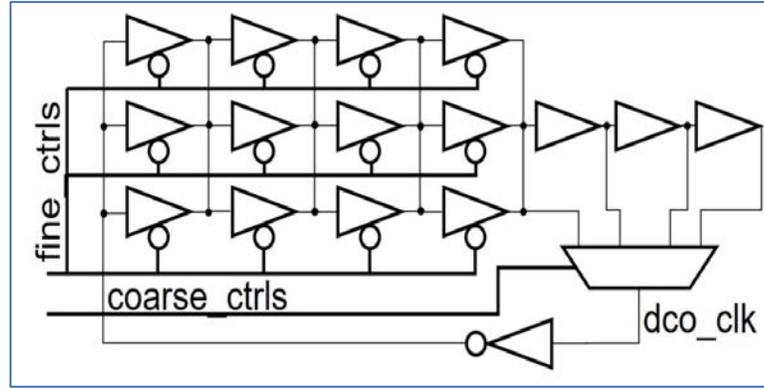
Timespot1: TDC

Fully digital design, standard-cell based, Vernier scheme

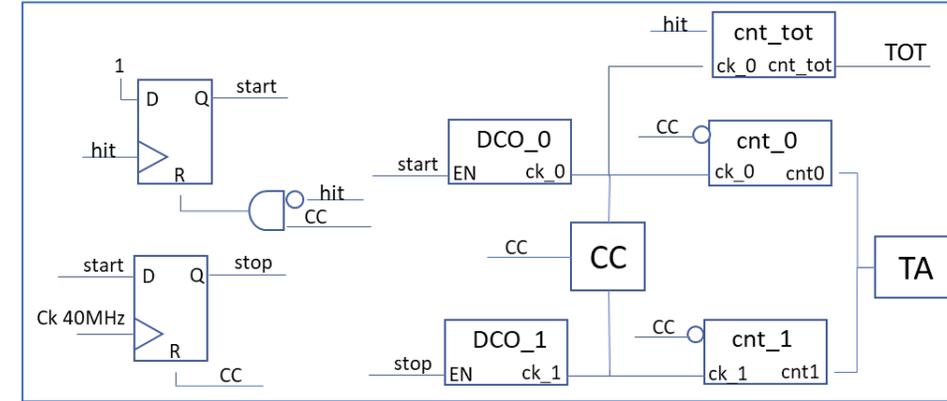


To maximize sustainable rate, 1 TDC per pixel channel has been integrated

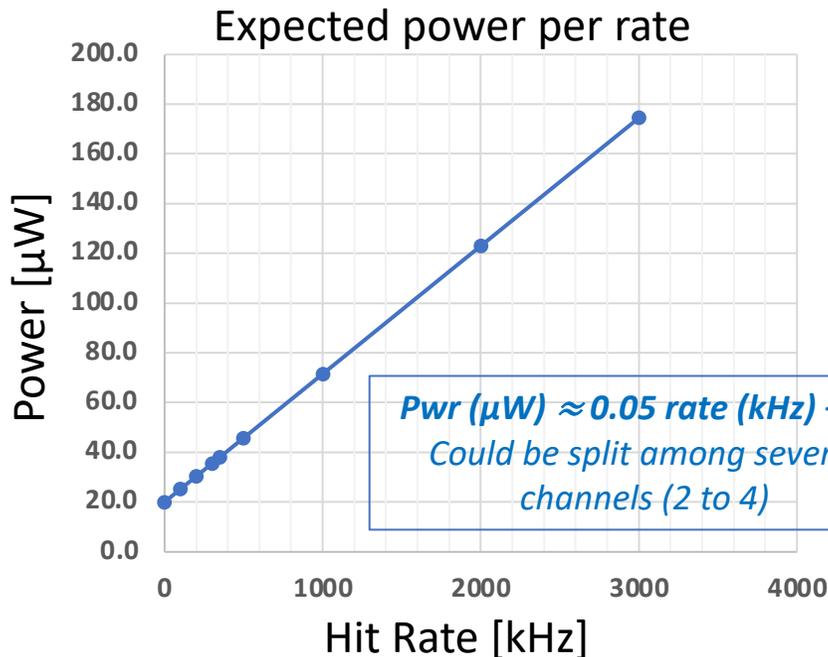
Max input rate = 3 MHz
23 bits output word (ToA + ToT)
ToT resolution \approx 1 ns



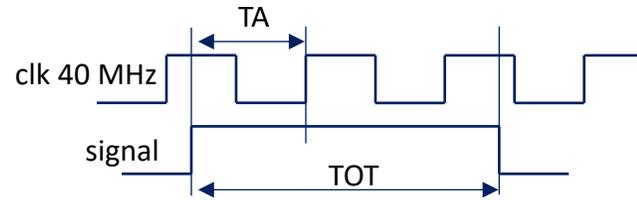
DCO scheme



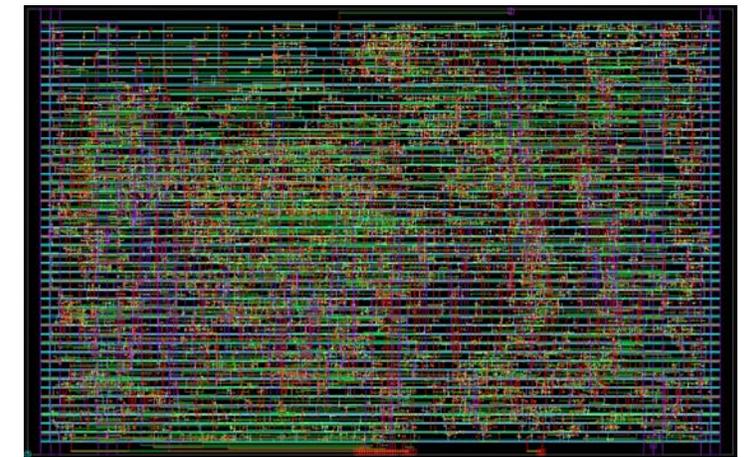
High resolution, "low" consumption TDC based on 2 DCOs and a Vernier architecture



$Pwr (\mu W) \approx 0.05 \text{ rate (kHz)} + 20$
Could be split among several channels (2 to 4)



The TDC gives the phase of the signal wrt the 40MHz BX clock
4 levels of Vernier precision (Δf in DCOs) can be programmed.
Typical LSB from simulations = 12 ps

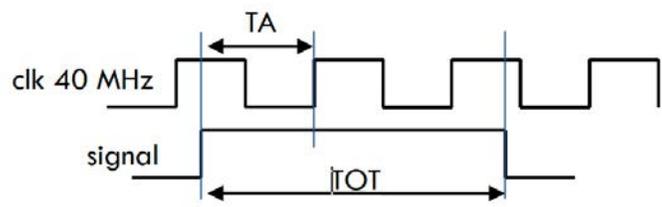
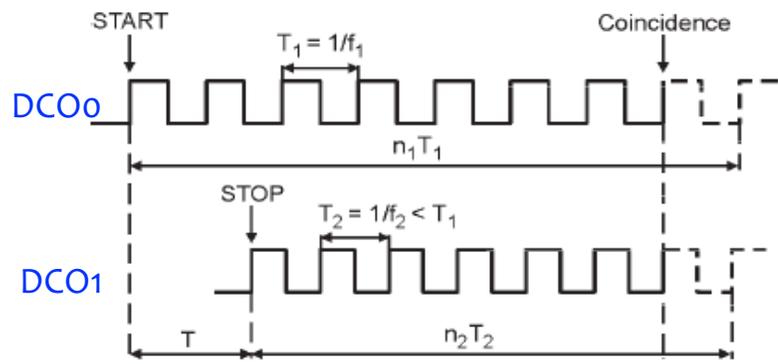


50x32 μm^2



Timespot1: TDC (2)

Circuit operations and criticalities



$$TA = (cnt_1 - 1)T_1 - (cnt_2 - 1)T_2$$

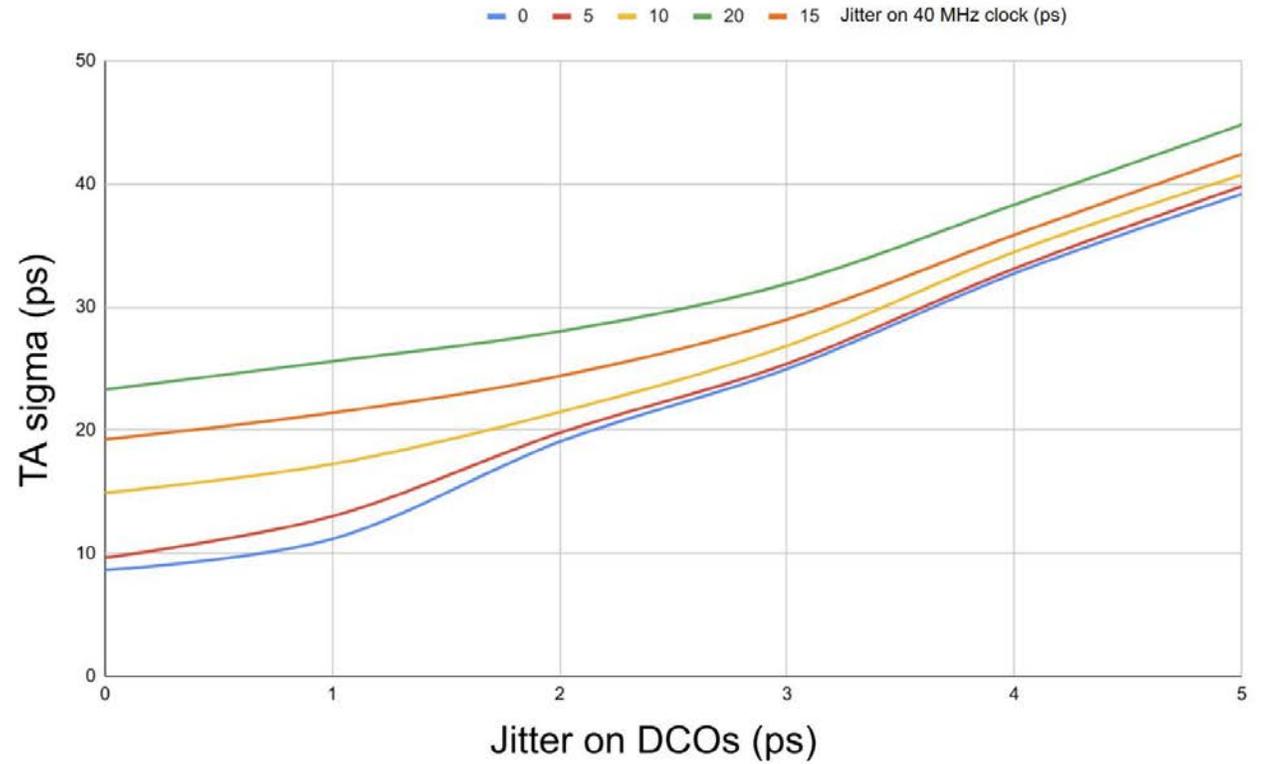
$$T_{conv_max} = \frac{T_1 \cdot T_2}{r(10ps)} \approx 100 \text{ ns}$$

$$T_{conv_max} = \frac{T_1 \cdot T_2}{r(30ps)} \approx 35 \text{ ns}$$

Set LSB

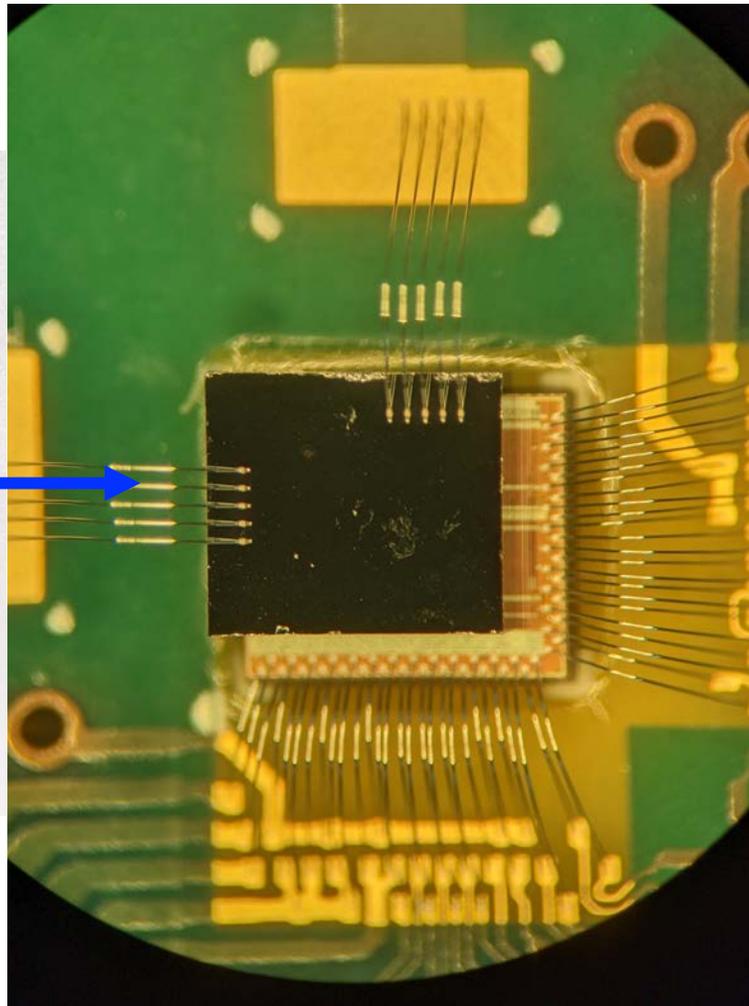
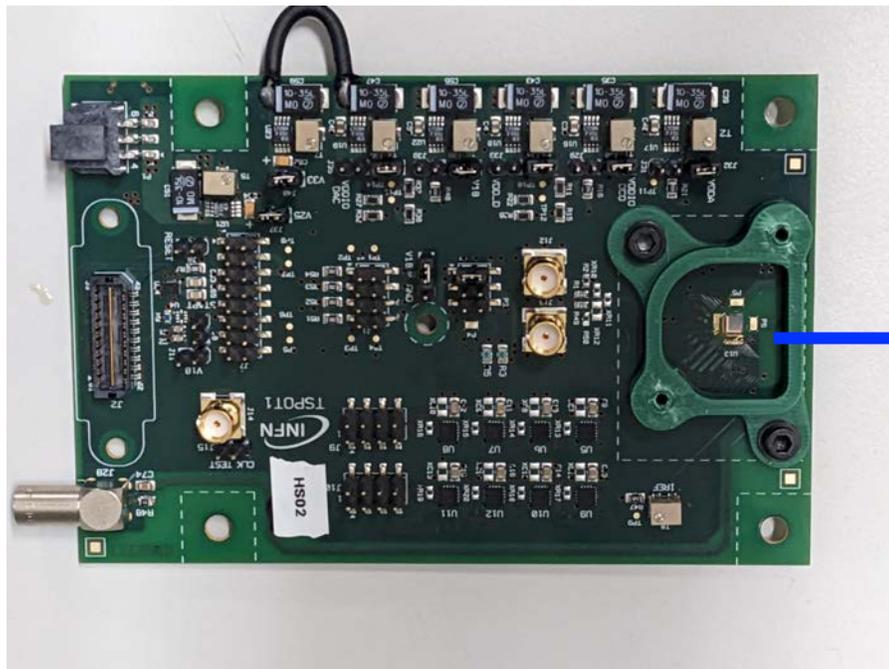
- TDC requirements:
 - Time of Arrival (TA): 30ps rms overall
 - Less than 15ps each contribution (Det. – AFE – TDC)
 - TDC LSB < 50ps
 - Time Over Threshold: LSB around 1ns or less
 - Max TOT < 200ns
- Vernier Architecture DCOs Frequency: ~ 1GHz
- DCO's is switched off after measurements
- The resolution does not depend on the periods but on their difference Δf
- Max conversion time depends on DCO Periods: Larger periods mean larger conversion time

The final TDC resolution depends on the jitters of the 40 MHz clock and of the DCO

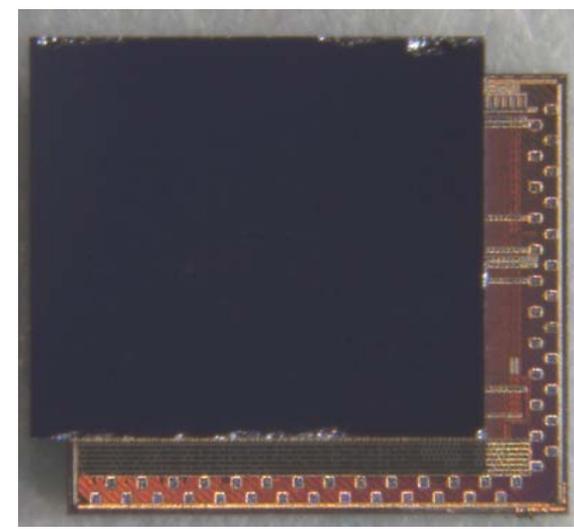


(not)hybridized devices

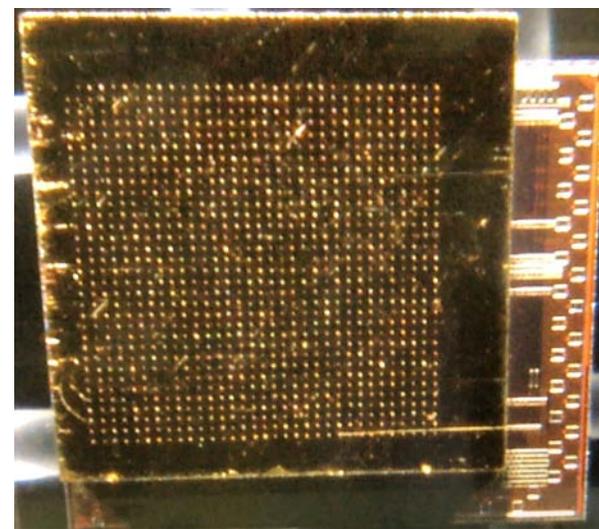
same test PCB



Timespot1 on 3D-trench silicon matrix



Timespot1 on 3D-column diamond matrix

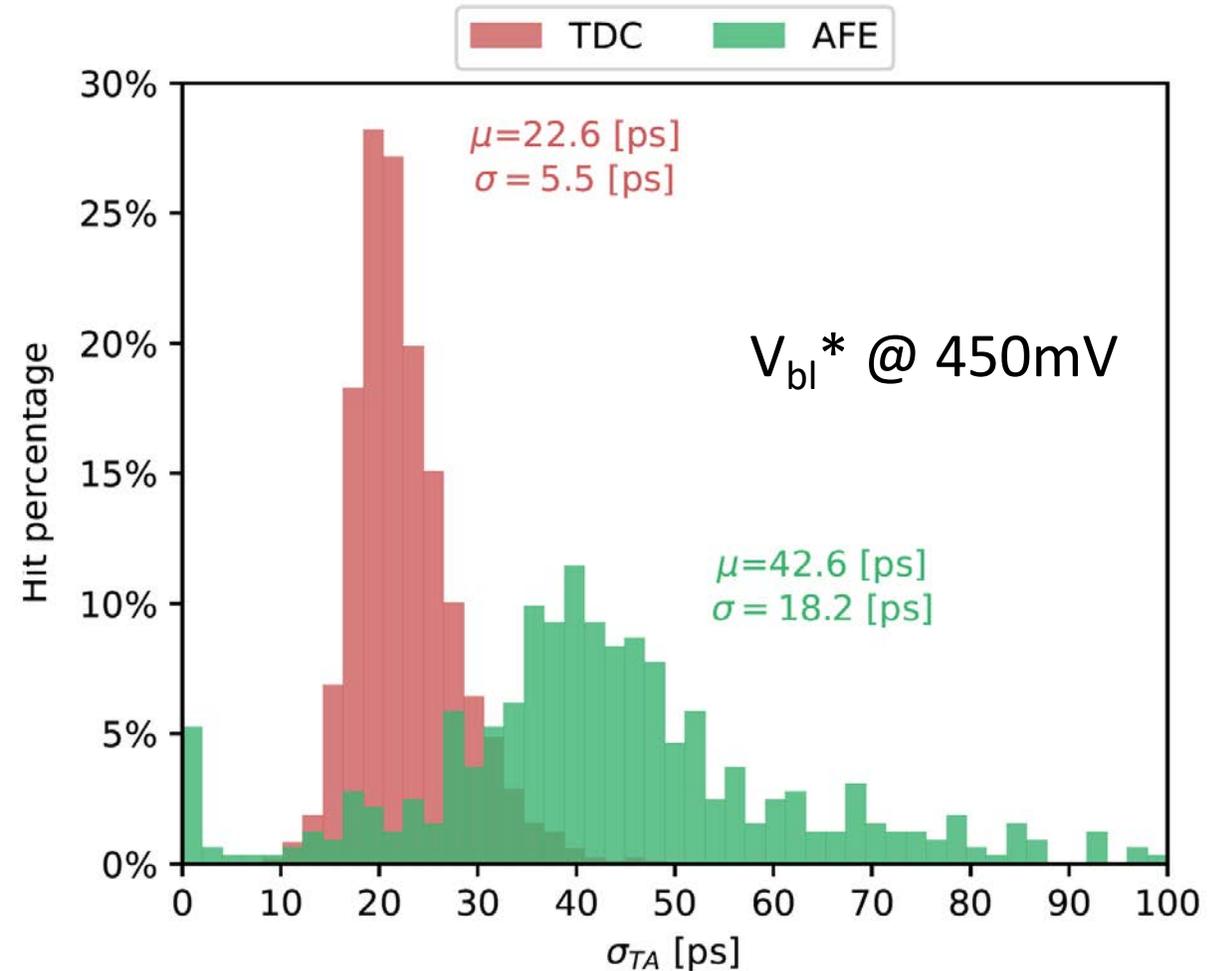


The test-bench PCB (named TSPOT1) operates also as a tracking station in the demonstrator (test beam at SPS)

Pixel characterization

Time resolution (no sensor)

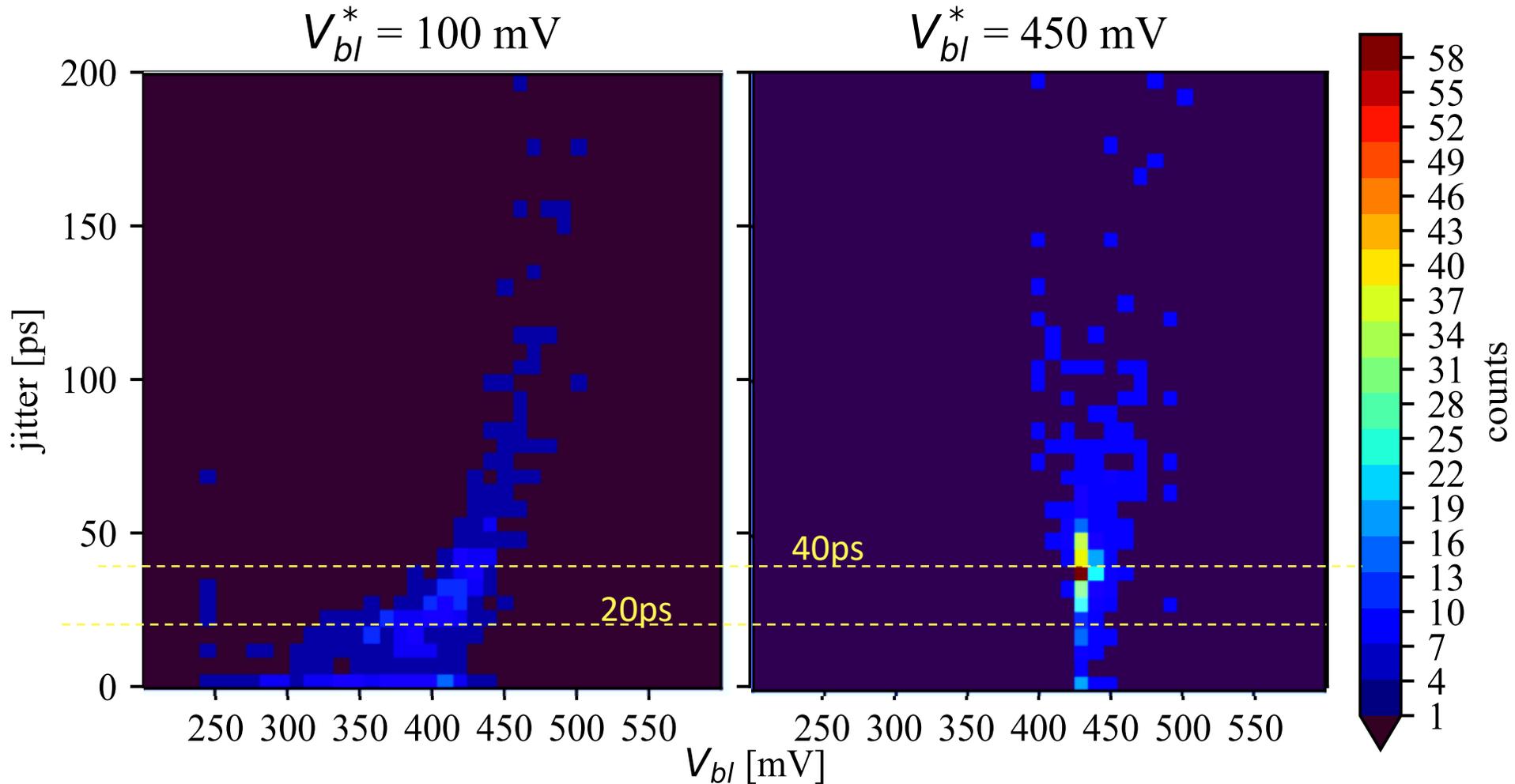
- The **TDC** has a typical $\sigma_t \approx 20$ ps, with a dispersion around 5 ps. No improvements are visible when increasing the Vernier precision (DCO jitter limit?)
- The AFE σ_t is **intrinsically better than 20 ps** but an identified **bug** in the Offset Compensation of the LED spoils σ_t in most of the channels (see next slide).
- In general, issues which are extrinsic to circuit design limit the very good resolution at the pixel level (clock distribution, OC bug). The pixel circuit **design appears adequate** to system requirements.
- Keeping uniformity under control across the ASIC area is particularly critical for timing performance in this technology



@ 12 μ W on AFE

Pixel: the Analog Front End

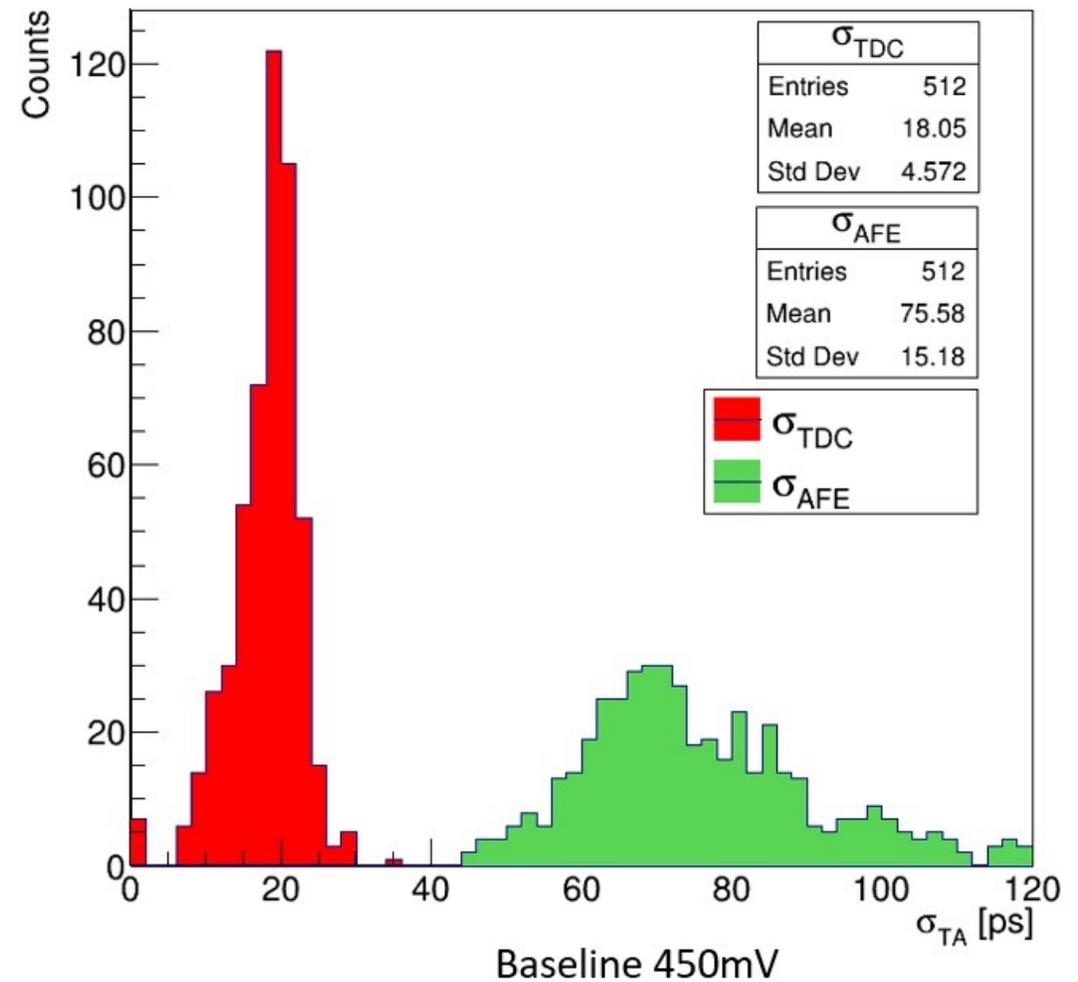
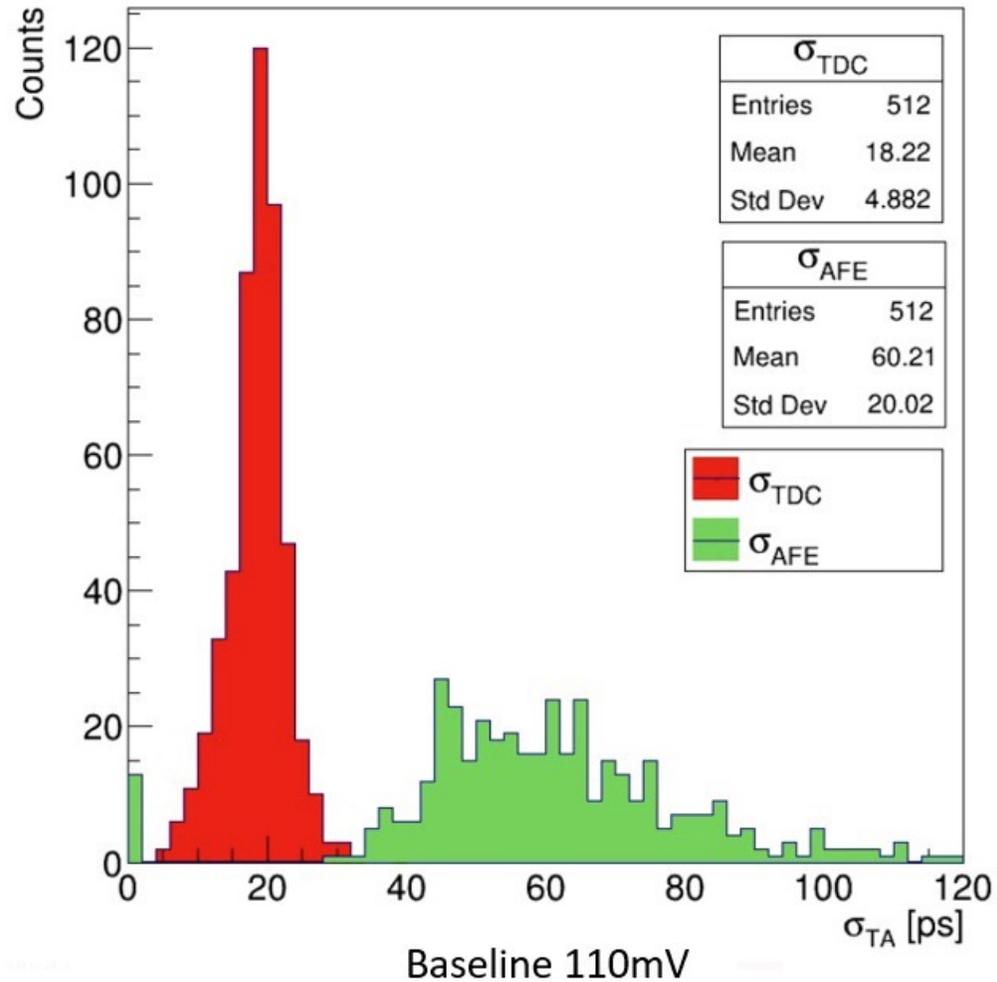
inadequate Offset Compensation



- When V_{bl} is set at low values, in most of the channels, the OC circuit fails to charge the memory capacitance C_{OC} .
- The discriminator is forced to work at high voltages, where it is band-limited
- The timing performance is heavily degraded

Hybridized devices

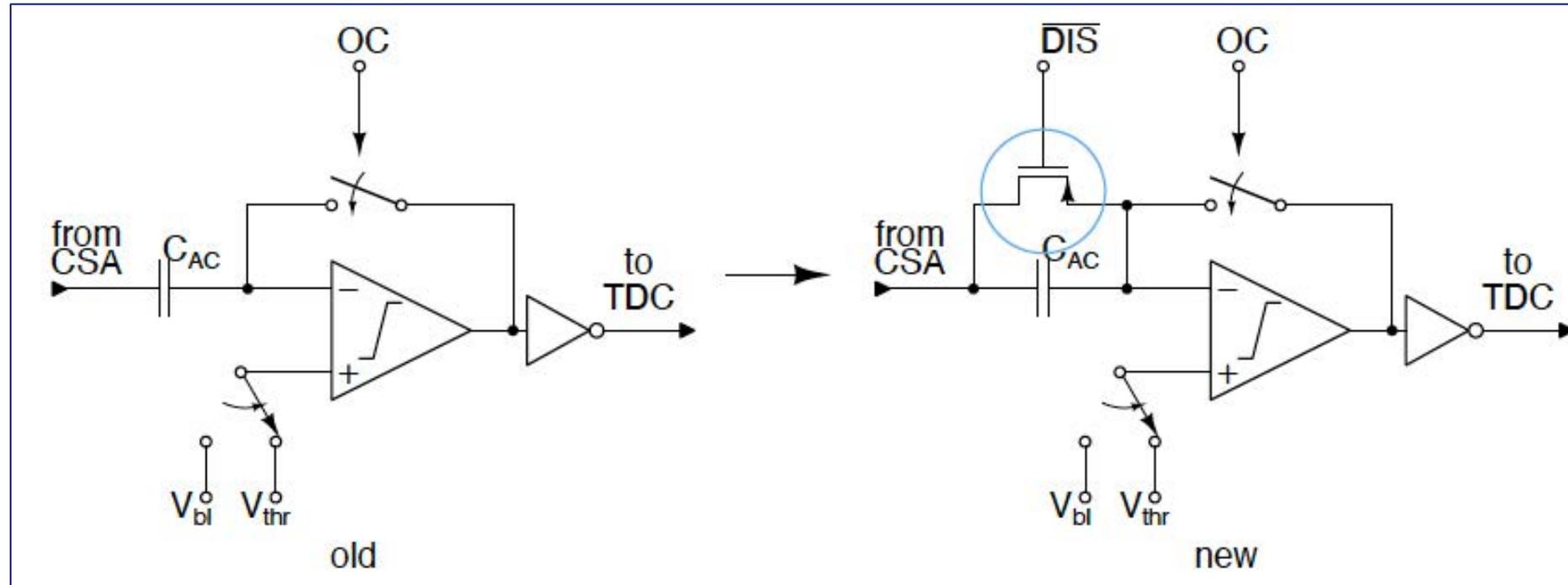
time resolution (2 fC pulses) – 2



Consistent behaviour with worsening of timing performance (C_{in})

A remedy

to the inadequate Offset Compensation

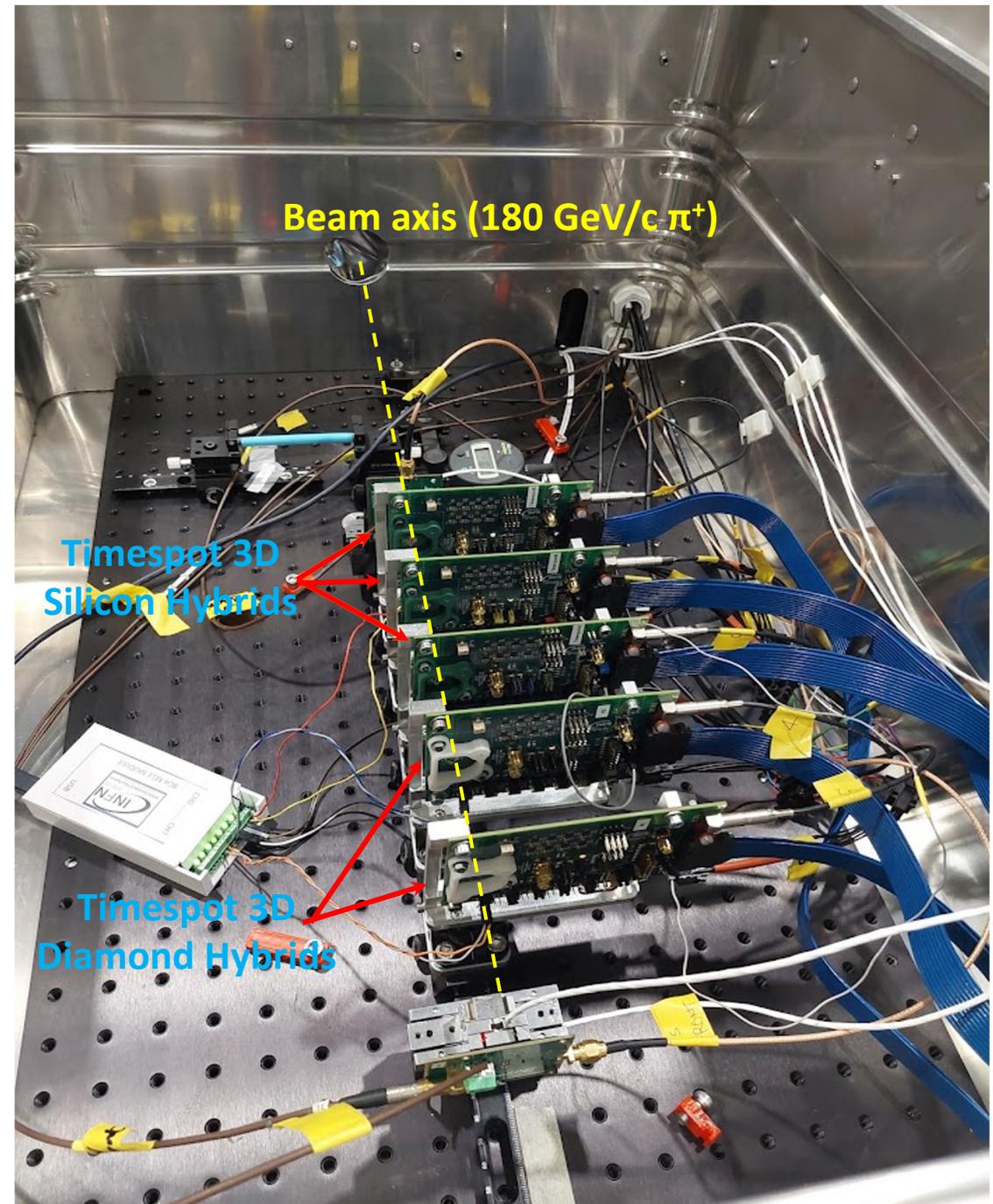
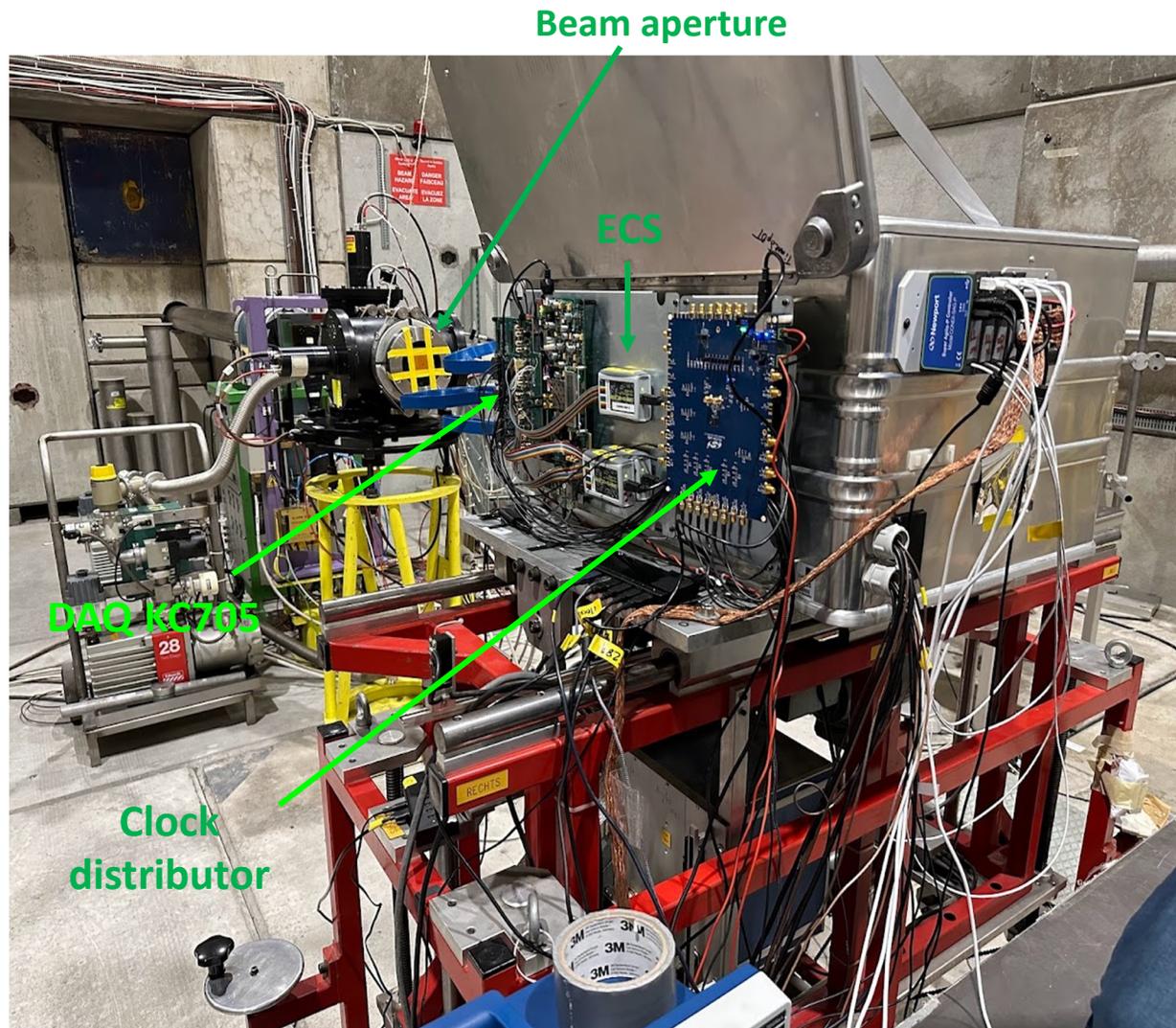


L. Piccolo INFN Torino

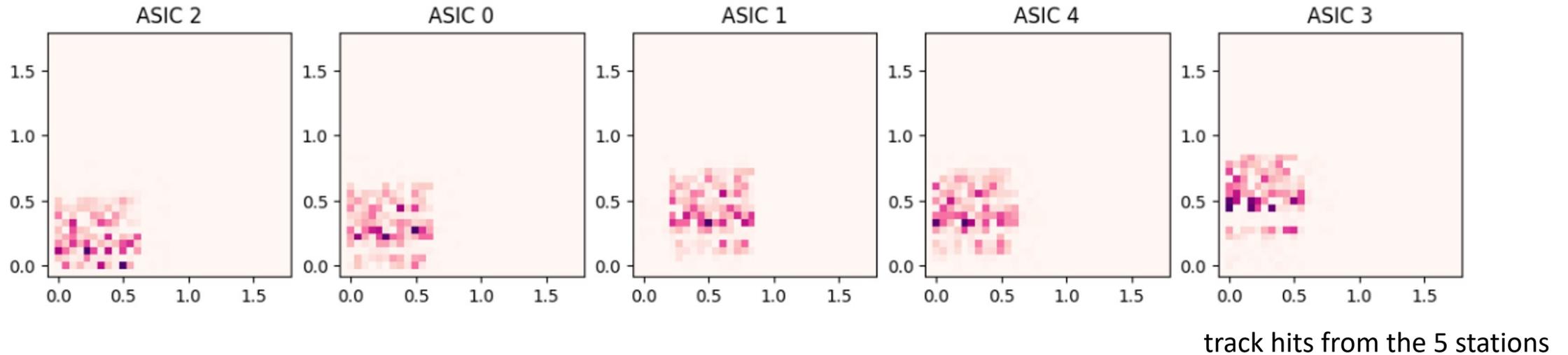
- Add a reset to force C_{AC} discharge
- Make the threshold setting switches CMOS (they were changed to PMOS for increasing ad-hardness)
- Use larger transistors to limit the post irradiation off-current.
- **More radically: switch to settable individual thresholds (DACs)**

TEST beam @SPS, May 2023

A tracker demonstrator (5 stations)



Preliminary results from the TimeSPOT telescope tests



1. **First ever tracks with a 28-nm based system** were acquired and reconstructed.
2. The space-tracking was satisfactory. **Tracking efficiency was as expected** ($\approx 80\%$ of geometrical efficiency, see L. Anderlini's talk @FAST May 2023, *Recent results on 3D diamond pixel detectors for 4D-tracking*)
3. Several aspects related to **system operation** have been explored and **better understood**. They give extremely **useful suggestions** for the next ASIC developments
4. The tests have been **dominated by system issues**:
 - The silicon hybrids were not biased properly, due to high leakage current in the sensor matrix, probably due to un-bonded pixels
 - The ASIC matrix was not fully operated, as this caused instabilities in DAQ. Only $\frac{1}{4}$ of the matrix was switched on
 - A circuit metastability bug on the TDCs was identified, causing them to stuck often (need of global reset to restart)
5. **First-sight results on timing performance appear much poorer than expected** (≈ 200 ps). Detailed analysis is in progress.

Lessons learned, conclusions and perspectives

- The **TimeSPOT ASIC** has been only a **first step** on the hard climb of high intensity 4D-tracking. Many things have been understood and many issues are still to be solved
- At the pixel level, we found **good circuit solutions** both for AFE and TDC, which will be basically confirmed (with some improvements) in the next version of the ASIC. A few bugs were identified and already corrected at the design level.
- In the next design we will tendentially **simplify** front-end circuits as much as possible (our «zen principle»). Complexity is a nest for bugs. A single high-resolution circuit is a radically different task than a **high resolution system made of million of channels working together**.
- A high-intensity complex test @SPS was important to further **stress the devices** and reveal specific issues to care about
- Internal and external timing and in general **global routing** (both power and clock) was not completely under control in the Timespot1. These are extremely delicate aspects which will considerably **worsen on larger size devices**. Verification techniques are decisive for the success of such designs and mandatory on nominal-size ASICs.
- A new ASIC is in preparation, where the architecture will be drastically changed, and the **global organization «localized»** by means of vertical interconnections (**TSV**), *but this is matter for a different talk.*

